Supporting Information

Temperature Controlled Tunable Emission of Bi3+-doped Rb2SnCl6 All-

inorganic Vacancy Ordered Lead-free Perovskite for Advanced

Anticounterfeiting

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Figure S1. (a) PL spectra of Bi³⁺-doped Rb₂SnCl₆ with different Bi³⁺ feeding ratios, excitation by 365 nm. (b) Peak position and peak intensity for 450 nm with Bi³⁺ concentration.



Figure S2. PL spectra image (a) and sample image under UV lamp (b) at various annealing temperatures from 50 to 220 °C, excitation by 365 nm.



Figure S3. PL spectra for PLQY of 8% Bi³⁺-doped Rb₂SnCl₆. (a) after 50 °C and (b) after 200 °C.



Figure S4. PL decay curves of Bi³⁺-doped Rb₂SnCl₆ at (a) after 50 °C, $\lambda_{ex} = 365$ nm and $\lambda_{em} = 453$ nm, and (b) after 200 °C, $\lambda_{ex} = 387$ nm and $\lambda_{em} = 500$ nm.



Figure S5. XRD patterns of 8% Bi³⁺-doped Rb₂SnCl₆ with different annealing temperatures.



Figure S6. (a-c) SEM image of the sample before annealing. (d-f) SEM image of the sample after annealing at 200 °C.



Figure S7. TGA and DSC spectra for Bi³⁺-doped Rb₂SnCl₆. (a) after 50 °C and (b) after 200 °C.



Figure S8. TGA-MS spectra for Bi³⁺-doped Rb₂SnCl₆. (a) after 50 °C and (b) after 200 °C.



Figure S9. XRD patterns after heat treatment at 400°C.



FigureS10. Band gap patterns of 8% Bi³⁺-doped Rb₂SnCl₆ with different annealing temperatures.